

MTE8080N3

Features

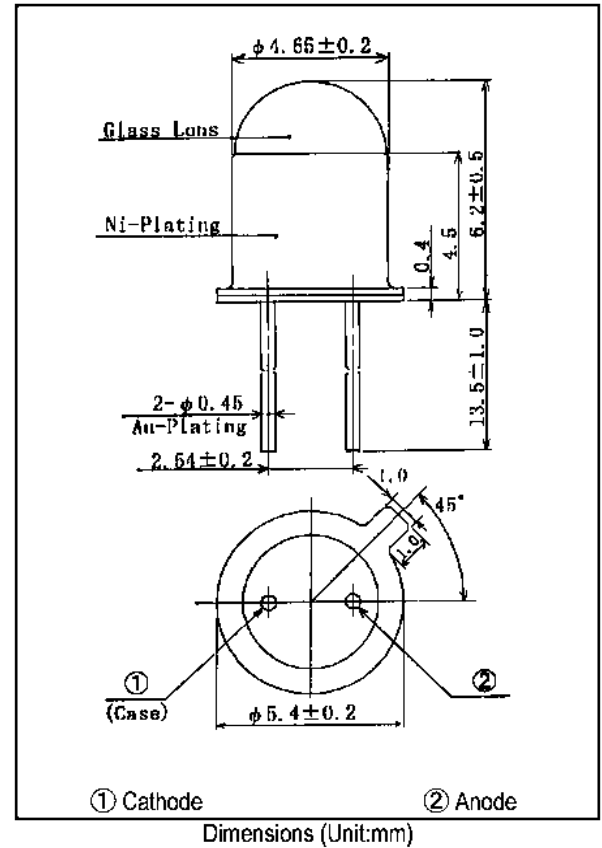
High Output Power
High Reliability in Demanding Environments
Narrow Beam Angle

Applications

Optical Emitters
Optical Switches

Maximum Ratings (Ta=25°C)

Characteristic	Symbol	Max.	Test Condition	Unit
Forward Current	I _F	100	–	mA
Pulsed Forward Current	I _{FP}	1.00	tw=10μS T=10mS	A
Reverse Voltage	V _R	5	–	V
Power Dissipation	P _D	180.00	–	mW
Operating Temperature	T _{opr}	–20 ~ +85	–	°C
Storage Temperature	T _{stg}	–30 ~ +100	–	°C
Junction Temperature	T _j	100	–	°C
Soldering Temperature	T _{sol}	260	for 3 sec. max	°C



Opto-Electrical Characteristics (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F =50mA	–	1.45	1.80	V
Reverse Current	I _R	V _R =5V	–	–	10	μA
Power Output	PO	I _F =50mA	–	9.00	–	mW
Half Intensity Beam Angle	θ	–	–	± 15°	–	deg.
Peak Wavelength	λ _p	I _F =50mA	–	880	–	nm
Spectral Line Half Width	Δλ	I _F =50mA	–	60	–	nm
Rise Time	T _r	I _{FP} =50mA	–	1.50	–	μs
Fall Time	T _f	I _{FP} =50mA	–	.80	–	μs
Temp Coefficient of PO	P/T	I _F =10mA	–	–.50	–	%/°C
Temp Coefficient of V _F	V/T	I _F =10mA	–	–1.50	–	mV/°C
Junction Capacitance	C _j	1 MHz, V=0V	–	15	–	pF

